

ABSTRACT:

To refine a semiconductor device (100), in particular a S[ilicon]O[n]I[nsulator] device, comprising:

- at least one isolating layer (10) made of a dielectric material;
- at least one silicon substrate (20) arranged on said isolating layer (10);
- 5 - at least one component (30) integrated in the silicon substrate (20), which component has at least one slightly doped zone (34); as well as
- at least a first, in particular planar, metallization region (40) arranged between the isolating layer (10) and the component (30), in particular between the isolating layer (10) and the slightly doped zone (34) of the component (30), as well as a method of
- 10 manufacturing at least one semiconductor device (100) in such a manner that trouble-free operation also of slightly doped components (30), such as pnp transistors, is guaranteed in a SOI process transferred onto the insulator, it is proposed that at least a second, in particular planar, metallization region (42) is arranged on the side of the silicon substrate (20) facing away from the isolating layer (10), in the area of the component (30), particularly in the area
- 15 of the slightly doped zone (34) of the component (30).

Fig. 1